

MILITARY SPECIFICATION

MICROCIRCUITS, DIGITAL, ADVANCED CMOS,
NOR GATES, MONOLITHIC SILICON

This amendment forms a part of MIL-M-38510/751A, dated 29 June 1992, and is approved for use by all Departments and Agencies of the Department of Defense.

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4.2b.3, delete and substitute:

"3. $V_{CC} = 5.5 \text{ V} \pm 0.5 \text{ V}, -0.00 \text{ V}.$ "

4.2c.3, delete and substitute:

"3. $V_{CC} = 5.5 \text{ V} \pm 0.5 \text{ V}, -0.00 \text{ V}.$ "

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Table 1, Power dissipation capacitance, Max Limits column, delete "75" and substitute "50".

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4.4.5, delete and substitute:

" 4.4.5 Group E inspection. Group E inspection is required only for parts intended to be marked as radiation hardness assured (see 3.5 herein). RHA levels for device classes B and S shall be M, D, R, and H. RHA quality conformance inspection sample tests shall be performed at the RHA level specified in the acquisition document.

- a. End-point electrical parameters shall be as specified in table II herein.
- b. For device classes B and S, subgroups 1 and 2 in table V, method 5005 of MIL-STD-883 shall be tested as appropriate for device construction.
- c. When specified in the purchase order or contract, a copy of the RHA delta limits shall be supplied.
- d. RHA tests for device classes B and S for levels M, D, R, and H shall be performed through each level to determine at what levels the devices meet the RHA requirements. These RHA tests shall be performed for initial qualification and after design or process changes which may affect the RHA performance of the device.
- e. Prior to irradiation, each selected sample shall be assembled in its qualified package. It shall pass the specified group A electrical parameters in table I for subgroups specified in table II herein.

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- f. For device classes B and S, the devices shall be subjected to radiation hardness assured tests as specified in MIL-M-38510 for the RHA level being tested. All device classes must meet the postirradiation end-point electrical parameter limits as defined in table I at $T_A = +25^\circ\text{C} \pm 5^\circ\text{C}$, after exposure, to the subgroups specified in table II herein.

4.4.5.1 Total dose irradiation testing. Total dose irradiation testing shall be performed in accordance with MIL-STD-883, method 1019, and as specified herein. Prior to and during total dose irradiation characterization and testing, the devices for characterization shall be biased so that 50 percent are at inputs high and 50 percent are at inputs low, and the devices for testing shall be biased to the worst case condition established during characterization. Devices shall be biased as follows:

- a. Inputs tested high, $V_{CC} = 5.5 \text{ V dc } +5\%$, $R_{CC} = 10\Omega +20\%$, $V_{IN} = 5.0 \text{ V dc } +5\%$, $R_{IN} = 1 \text{ k}\Omega +20\%$, and all outputs are open.
- b. Inputs tested low, $V_{CC} = 5.5 \text{ V dc } +5\%$, $R_{CC} = 10\Omega +20\%$, $V_{IN} = 0.0 \text{ V dc}$, $R_{IN} = 1 \text{ k}\Omega +20\%$, and all outputs are open.

4.4.5.1.1 Accelerated aging test. Accelerated aging shall be performed on class B and S devices requiring an RHA level greater than 5K rads (Si). The post-anneal end point electrical parameter limits shall be as specified in table I herein and shall be the preirradiation end point electrical parameter limit at $25^\circ\text{C} \pm 5^\circ\text{C}$. Testing shall be performed at initial qualification and after any design or process changes which may effect the RHA response of the device."

CONCLUDING MATERIAL

Custodians:

Army - ER
Navy - EC
Air Force - 17
NASA - NA

Review activities:

Army - AR, MI
Air Force - 19, 85, 99
DLA - ES

User activities:

Army - SM
Navy - AS, CG, MC, OC, SH

Preparing activity:
Air Force - 17

Agent:
DLA - ES

(Project 5962-1326)